L Number	Hits	Search Text	DB -	
260	1259	(pattern wire wiring layer)) and (power	USPAT; US-PGPUB;	Time stamp 2003/05/17 16:20
 	316	and (ground grounding)) 	EPO; JPO; DERWENT	
201	3.0	(pattern wire wiring laver)) and (nower	USPAT; US-PGPUB;	2003/05/17 16:20
 	69	and (ground grounding))) and (silicon nearl substrate)	EPO; JPO; DERWENT	
	CJ	((semiconductor and ((dummy shield\$3) nearl (pattern wire wiring layer)) and (power and (ground grounding))) and	USPAT; US-PGPUB;	2003/05/17 16:22
i		(silicon near! substrate)) and (dummy near! (pattern wire wiring layer))	EPO; JPO; DERWENT	
263 	2541 j	designing near device	USPAT;	2003/05/17 16:23
İ	 		US-PGPUB; EPO; JPO; DERWENT	
264	260 	(semiconductor and ((dummy shield\$3) nearl (pattern wire wiring layer)) and (power	USPAT;	2003/05/17 16:23
	 	<pre>and (ground grounding))) and (dummy nearl (pattern wire wiring layer))</pre>	EPO; JPO; DERWENT	İ
265	3	(designing near device) and ((semiconductor and ((dummy shield\$3)	USPAT; US-PGPUB;	2003/05/17 16:23
	į	nearl (pattern wire wiring layer)) and (power and (ground grounding)) and (dummy	EPO; JPO; DERWENT	
	<u>_</u>	nearl (pattern wire wiring layer)))	<u> </u>	